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October 2014

# CNY171M, CNY172M, CNY173M, CNY174M, CNY17F1M, CNY17F2M, CNY17F3M, CNY17F4M, MOC8106M 6-Pin DIP High BV<sub>CEO</sub> Phototransistor Optocouplers

### **Features**

- High BV<sub>CEO</sub>: 70 V Minimum (CNY17XM, CNY17FXM, MOC8106M)
- Closely Matched Current Transfer Ratio (CTR)
   Minimizes Unit-to-Unit Variation
- Current Transfer Ratio In Select Groups
- Very Low Coupled Capacitance Along With No Chip-to-Pin 6 Base Connection for Minimum Noise Susceptability (CNY17FXM, MOC8106M)
- Safety and Regulatory Approvals:
  - UL1577, 4,170 VAC<sub>RMS</sub> for 1 Minute
  - DIN-EN/IEC60747-5-5, 850 V Peak Working Insulation Voltage

## **Applications**

- Power Supply Regulators
- Digital Logic Inputs
- Microprocessor Inputs
- Appliance Sensor Systems
- Industrial Controls

## **Description**

The CNY17XM, CNY17FXM, and MOC8106M devices consist of a gallium arsenide infrared emitting diode coupled with an NPN phototransistor in a dual in-line package.

## **Package Outlines**

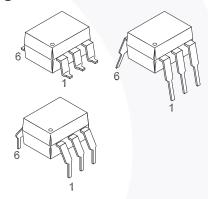


Figure 1. Package Outlines

## **Schematics**

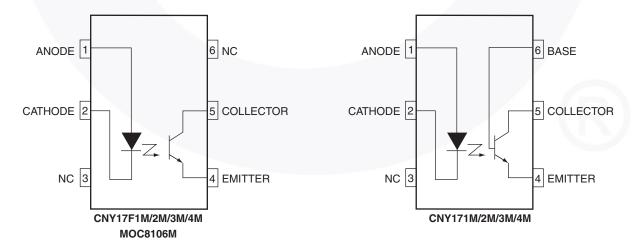


Figure 2. Schematics

## **Safety and Insulation Ratings**

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter	Characteristics	
Installation Classifications per DIN VDE	< 150 V <sub>RMS</sub>	I–IV
0110/1.89 Table 1, For Rated Mains Voltage	< 300 V <sub>RMS</sub>	I–IV
Climatic Classification		55/100/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
\/	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$ , Type and Sample Test with $t_m = 10$ s, Partial Discharge < 5 pC	1360	V <sub>peak</sub>
V <sub>PR</sub>	Input-to-Output Test Voltage, Method B, V <sub>IORM</sub> x 1.875 = V <sub>PR</sub> , 100% Production Test with t <sub>m</sub> = 1 s, Partial Discharge < 5 pC	1594	V <sub>peak</sub>
V <sub>IORM</sub>	Maximum Working Insulation Voltage	850	V <sub>peak</sub>
V <sub>IOTM</sub>	Highest Allowable Over-Voltage	6000	V <sub>peak</sub>
	External Creepage	≥ 7	mm
	External Clearance	≥ 7	mm
	External Clearance (for Option TV, 0.4" Lead Spacing)	≥ 10	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.5	mm
T <sub>S</sub>	Case Temperature <sup>(1)</sup>	175	°C
I <sub>S,INPUT</sub>	Input Current <sup>(1)</sup>	350	mA
P <sub>S,OUTPUT</sub>	Output Power <sup>(1)</sup>	800	mW
R <sub>IO</sub>	Insulation Resistance at T <sub>S</sub> , V <sub>IO</sub> = 500 V <sup>(1)</sup>	> 10 <sup>9</sup>	Ω

#### Note:

1. Safety limit values – maximum values allowed in the event of a failure.

## **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameters	Value	Units
TOTAL DE	VICE		
T <sub>STG</sub>	Storage Temperature	-40 to +125	°C
T <sub>A</sub>	Ambient Operating Temperature	-40 to +100	°C
T <sub>J</sub>	Junction Temperature	-40 to +125	°C
T <sub>SOL</sub>	Lead Solder Temperature	260 for 10 seconds	°C
	Total Device Power Dissipation @ 25°C (LED plus detector)	270	mW
$P_{D}$	Derate Linearly From 25°C	2.94	mW/°C
EMITTER			
I <sub>F</sub>	Continuous Forward Current	60	mA
V <sub>R</sub>	Reverse Voltage	6	V
I <sub>F</sub> (pk)	Forward Current – Peak (1 µs pulse, 300 pps)	1.5	Α
Б	LED Power Dissipation 25°C Ambient	120	mW
$P_{D}$	Derate Linearly From 25°C	1.41	mW/°C
DETECTO	R		
I <sub>C</sub>	Continuous Collector Current	50	mA
V <sub>CEO</sub>	Collector-Emitter Voltage	70	V
V <sub>ECO</sub>	Emitter Collector Voltage	7	V
	Detector Power Dissipation @ 25°C	150	mW
$P_{D}$	Derate Linearly from 25°C	1.76	mW/°C

## **Electrical Characteristics**

 $T_A = 25$ °C unless otherwise specified.

## **Individual Component Characteristics**

Symbol	Parameters	Test Conditions	Device	Min.	Тур.	Max.	Units	
EMITTER	EMITTER							
		I <sub>F</sub> = 10 mA	All Devices	1.0	1.15	1.50	V	
$V_{F}$	Input Forward Voltage	I <sub>F</sub> = 60 mA	CNY17XM, CNY17FXM	1.0	1.35	1.65	V	
CJ	Capacitance	V <sub>F</sub> = 0 V, f = 1.0 MHz	All Devices		18		pF	
I <sub>R</sub>	Reverse Leakage Current	V <sub>R</sub> = 6 V	All Devices		0.001	10	μA	
DETECTO	OR			•	•	•		
	Breakdown Voltage							
$BV_CEO$	Collector-to-Emitter	$I_C = 1 \text{ mA}, I_F = 0$	All Devices	70	100		V	
BV <sub>CBO</sub>	Collector-to-Base	I <sub>C</sub> = 10 μA, I <sub>F</sub> = 0	CNY17XM	70	120		V	
BV <sub>ECO</sub>	Emitter-to-Collector	$I_E = 100 \mu A, I_F = 0$	All Devices	7	10		V	
1/1	Leakage Current			4				
$I_{CEO}$	Collector-to-Emitter	$V_{CE} = 10 \text{ V}, I_{F} = 0$	All Devices		1	50	nA	
I <sub>CBO</sub>	Collector-to-Base	V <sub>CB</sub> = 10 V, I <sub>F</sub> = 0	CNY17XM			20	nA	
	Capacitance							
$C_{CE}$	Collector-to-Emitter	V <sub>CE</sub> = 0, f = 1 MHz	All Devices		8		pF	
C <sub>CB</sub>	Collector-to-Base	V <sub>CB</sub> = 0, f = 1 MHz	CNY17XM		20		pF	
C <sub>EB</sub>	Emitter-to-Base	V <sub>EB</sub> = 0, f = 1 MHz	CNY17XM		10		pF	

## **Transfer Characteristics**

Symbol	Parameters	Test Conditions	Device	Min.	Тур.	Max.	Units
COUPLE	D					•	
CTR Current Transfer Ratio	I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 10 V	MOC8106M	50		150	%	
		I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 5 V	CNY171M, CNY17F1M	40		80	%
		I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 5 V	CNY172M, CNY17F2M	63		125	%
	riado	I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 5 V	CNY173M, CNY17F3M	100		200	%
		I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 5 V	CNY174M, CNY17F4M	160		320	%
V <sub>CE(SAT)</sub>	Collector-Emitter Saturation Voltage	$I_C = 0.5 \text{ mA}, I_F = 5 \text{ mA}$	MOC8106M	0.0		0.4	V
		$I_C = 2.5 \text{ mA}, I_F = 10 \text{ mA}$	CNY17XM/CNY17FXM			0.4	V

# **Electrical Characteristics** (Continued)

 $T_A = 25$ °C unless otherwise specified.

## **AC Characteristics**

Symbol	Parameters	Test Conditions	Device	Min.	Тур.	Max.	Units	
NON-SAT	NON-SATURATED SWITCHING TIME							
t <sub>on</sub>	Turn-On Time	$I_C$ = 2.0 mA, $V_{CC}$ = 10 V, $R_L$ = 100 $\Omega$	All Devices		2.0	10.0	μs	
t <sub>off</sub>	Turn-Off Time	$I_C$ = 2.0 mA, $V_{CC}$ = 10 V, $R_L$ = 100 $\Omega$	All Devices		3.0	10.0	μs	
t <sub>d</sub>	Delay Time	$I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 75 \Omega$	CNY17XM/CNY17FXM			5.6	μs	
t <sub>r</sub>	Rise Time	$I_F$ = 10 mA, $V_{CC}$ = 5 V, $R_L$ = 75 $\Omega$	CNY17XM/CNY17FXM			4.0	μs	
ts	Storage Time	$I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 75 \Omega$	CNY17XM/CNY17FXM			4.1	μs	
t <sub>f</sub>	Fall Time	$I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 75 \Omega$	CNY17XM/CNY17FXM			3.5	μs	
SATURAT	TED SWITCHING	TIMES				•		
		$I_F = 20 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 1 \text{ k}\Omega$	CNY171M/F1M			5.5	μs	
t <sub>d</sub>	Delay Time	$I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 1 \text{ k}\Omega$	CNY172M/3M/4M CNY17F2M/F3M/F4M			8.0	μs	
		$I_F = 20 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 1 \text{ k}\Omega$	CNY171M/F1M			4.0	μs	
t <sub>r</sub>	Rise Time	$I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 1 \text{ k}\Omega$	CNY172M/3M/4M CNY17F2M/F3M/F4M			6.0	μs	
	The state of the s	$I_F = 20 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 1 \text{ k}\Omega$	CNY171M/F1M			34.0	μs	
t <sub>s</sub>	Storage Time	$I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 1 \text{ k}\Omega$	CNY172M/3M/4M CNY17F2M/F3M/F4M			39.0	μs	
		$I_F = 20 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 1 \text{ k}\Omega$	CNY171M/F1M			20.0	μs	
t <sub>f</sub>	Fall Time	$I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 1 \text{ k}\Omega$	CNY172M/3M/4M CNY17F2M/F3M/F4M			24.0	μs	

## **Isolation Characteristics**

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Units
V <sub>ISO</sub>	Input-Output Isolation Voltage	t = 1 Minute	4170			VAC <sub>RMS</sub>
C <sub>ISO</sub>	Isolation Capacitance	V <sub>I-O</sub> = 0 V, f = 1 MHz		0.2		pF
R <sub>ISO</sub>	Isolation Resistance	$V_{I-O} = \pm 500 \text{ VDC}, T_A = 25^{\circ}\text{C}$	10 <sup>11</sup>			Ω

# **Typical Performance Characteristics**

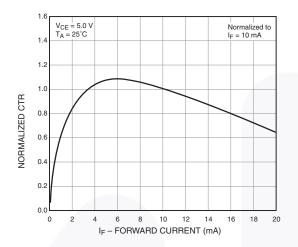


Figure 3. Normalized CTR vs. Forward Current

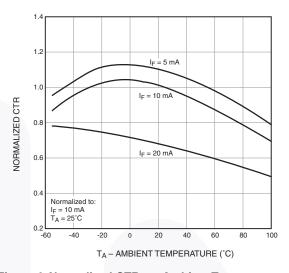


Figure 4. Normalized CTR vs. Ambient Temperature

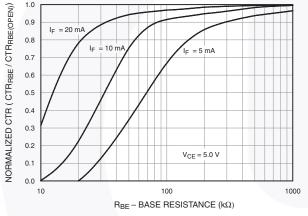


Figure 5. CTR vs. RBE (Unsaturated)

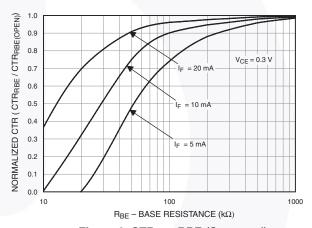


Figure 6. CTR vs. RBE (Saturated)

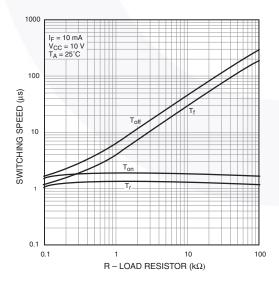


Figure 7. Switching Speed vs. Load Resistor

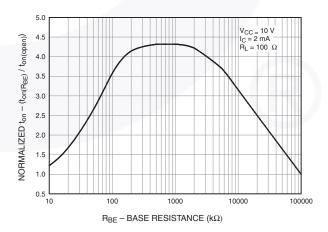
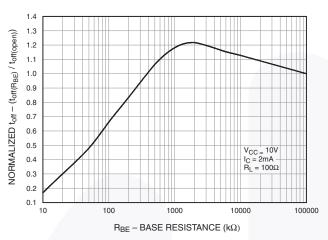


Figure 8. Normalized ton vs. RBE

# **Typical Performance Characteristics** (Continued)



1.8

1.7

2 1.6

HSW 1.5

1.5

1.7

TA = -55°C

TA = 100°C

1.1

1.0

1 10

1 100

IF - LED FORWARD CURRENT (mA)

Figure 9. Normalized toff vs. RBE

Figure 10. LED Forward Voltage vs. Forward Current

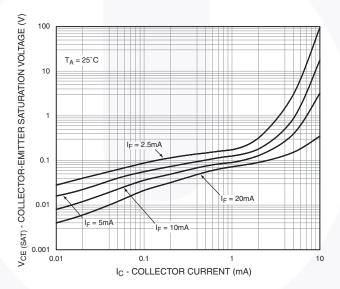


Figure 11. Collector-Emitter Saturation Voltage vs. Collector Current

# **Switching Test Circuit and Waveforms**

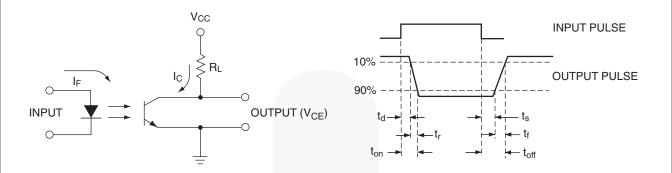


Figure 12. Switching Test Circuit and Waveforms

## **Reflow Profile**

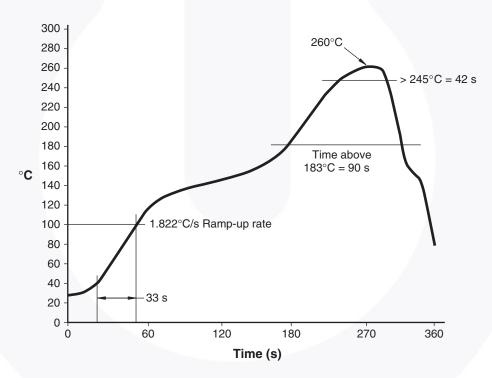


Figure 13. Reflow Profile

# **Ordering Information**

Part Number	Package	Packing Method
CNY171M	DIP 6-Pin	Tube (50 Units)
CNY171SM	SMT 6-Pin (Lead Bend)	Tube (50 Units)
CNY171SR2M	SMT 6-Pin (Lead Bend)	Tape and Reel (1000 Units)
CNY171TM	DIP 6-Pin, 0.4" Lead Spacing	Tube (50 Units)
CNY171VM	DIP 6-Pin, DIN EN/IEC60747-5-5 Option	Tube (50 Units)
CNY171SVM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	Tube (50 Units)
CNY171SR2VM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	Tape and Reel (1000 Units)
CNY171TVM	DIP 6-Pin, 0.4" Lead Spacing, DIN EN/IEC60747-5-5 Option	Tube (50 Units)

#### Note:

2. The product orderable part number system listed in this table also applies to the CNY17FXM product family and the MOC8106M device.

## **Marking Information**

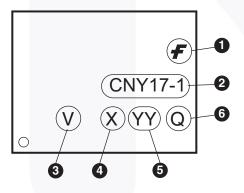
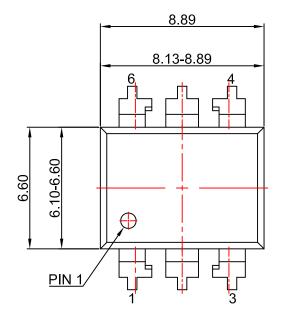
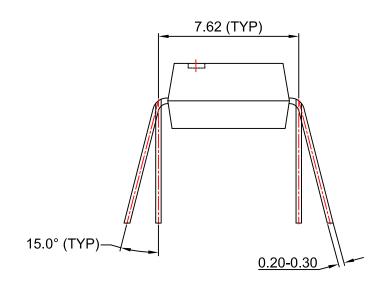


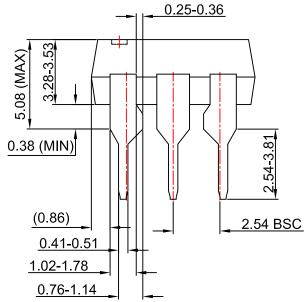
Figure 14. Top Mark

## **Table 1. Top Mark Definitions**

1	Fairchild Logo
2	Device Number
3	DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)
4	One-Digit Year Code, e.g., "4"
5	Digit Work Week, Ranging from "01" to "53"
6	Assembly Package Code



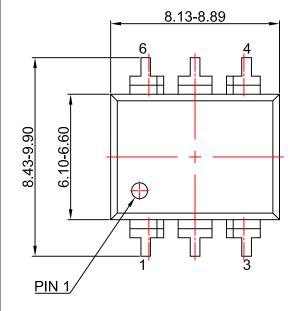


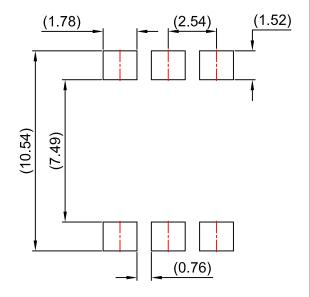


## NOTES:

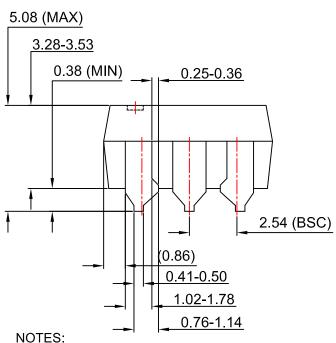
- A) NO STANDARD APPLIES TO THIS PACKAGE.
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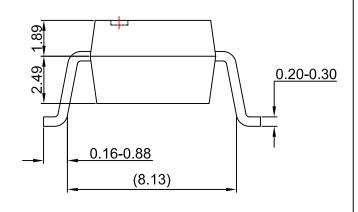






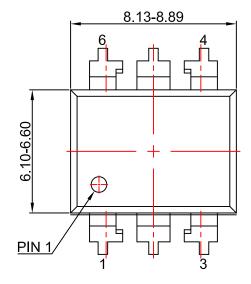
LAND PATTERN RECOMMENDATION

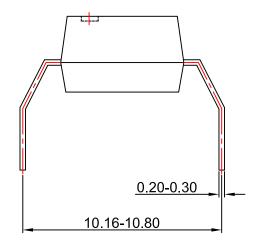


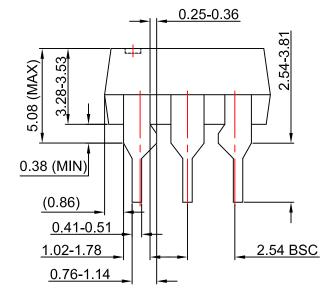


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Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

#### PRODUCT STATUS DEFINITIONS

#### **Definition of Terms**

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Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

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